

# ABSTRACT OF THE DISCLOSURE

A semiconductor laser element having an advantageous vertical light confinement efficiency, a low threshold current and a low element resistance is provided. The  
5 semiconductor laser element has a substrate and a stacked structure formed thereon, where the stacked structure comprises a buffer layer, an n-Al<sub>0.6</sub>Ga<sub>0.4</sub>As cladding layer, an n-Al<sub>0.47</sub>Ga<sub>0.53</sub>As cladding layer, an active layer, a p-Al<sub>0.47</sub>Ga<sub>0.53</sub>As first cladding layer, an Al<sub>0.55</sub>Ga<sub>0.45</sub>As etching  
10 stop layer, a p-Al<sub>0.47</sub>Ga<sub>0.53</sub>As second cladding layer, a p-Al<sub>0.6</sub>Ga<sub>0.4</sub>As third cladding layer, and a p-GaAs contact layer. The second and third cladding layers, and the contact layer are formed as a stripe-patterned ridge, and serve as a current injection regions. Both lateral portions of the ridge are  
15 filled with an n-type current blocking layer and serve as non-current-injection regions. Because the cladding layers on the active-layer-section side have a refractive index larger than that of the cladding layers disposed outward thereof, light leaked from the active layer section can  
20 efficiently be confined within the cladding layers on the active-layer-section side.